

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,105,208 B2
APPLICATION NO. : 10/699013
DATED : September 12, 2006
INVENTOR(S) : Craig M. Carpenter

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Col. 1, line 24 –

Replace “deposition (CVD) and atomic layer deposition (CVD). CVD”

With --deposition (CVD) and atomic layer deposition (ALD). CVD--

Col. 3, line 10 –

Replace “in the periodic table, namely, Al, Ga, In, Tl, Ge, Sn, Pb, Sb,”

With -- in the periodic table, namely, Al, Ga, In, Tl, Ge, Sn, Pb, Sb,--

Col. 3, line 64 –

Replace “forming other than One monolayer at a time by stacking of”

With -- forming other than one monolayer at a time by stacking of --

Col. 4, line 7 –

Replace “Traditional ALD can occur within an frequently-used”

With -- Traditional ALD can occur within frequently-used --

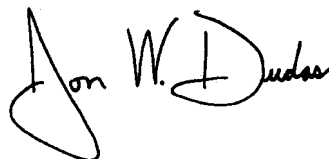
Col. 4, line 23 –

Replace “ CVD is commonly used to form non-selectively a complete,”

With --CVD is commonly used to form non-selectively complete,--

Signed and Sealed this

Twenty-fourth Day of July, 2007

A handwritten signature in black ink, appearing to read "Jon W. Dudas". The signature is stylized with a large, looped initial "J" and a distinct "D".

JON W. DUDAS

Director of the United States Patent and Trademark Office